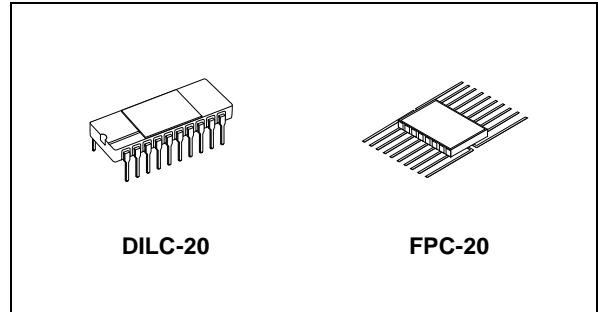


## RAD-HARD OCTAL BUS BUFFER WITH 3 STATE OUTPUTS (INVERTED)

- HIGH SPEED:  
 $t_{PD} = 9\text{ns}$  (TYP.) at  $V_{CC} = 6\text{V}$
- LOW POWER DISSIPATION:  
 $I_{CC} = 4\mu\text{A}$ (MAX.) at  $T_A=25^\circ\text{C}$
- HIGH NOISE IMMUNITY:  
 $V_{NIH} = V_{NIL} = 28\%$   $V_{CC}$  (MIN.)
- SYMMETRICAL OUTPUT IMPEDANCE:  
 $|I_{OHI}| = I_{OL} = 6\text{mA}$  (MIN)
- BALANCED PROPAGATION DELAYS:  
 $t_{PLH} \approx t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE:  
 $V_{CC}$  (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH 54 SERIES 540
- SPACE GRADE-1: ESA SCC QUALIFIED
- 50 krad QUALIFIED, 100 krad AVAILABLE ON REQUEST
- NO SEL UNDER HIGH LET HEAVY IONS IRRADIATION
- DEVICE FULLY COMPLIANT WITH SCC-9401-049

### DESCRIPTION

The 54HC540 is an advanced high-speed CMOS OCTAL BUS BUFFER (3-STATE) fabricated with silicon C<sup>2</sup>MOS technology. The M54HC541 is an inverting buffer.



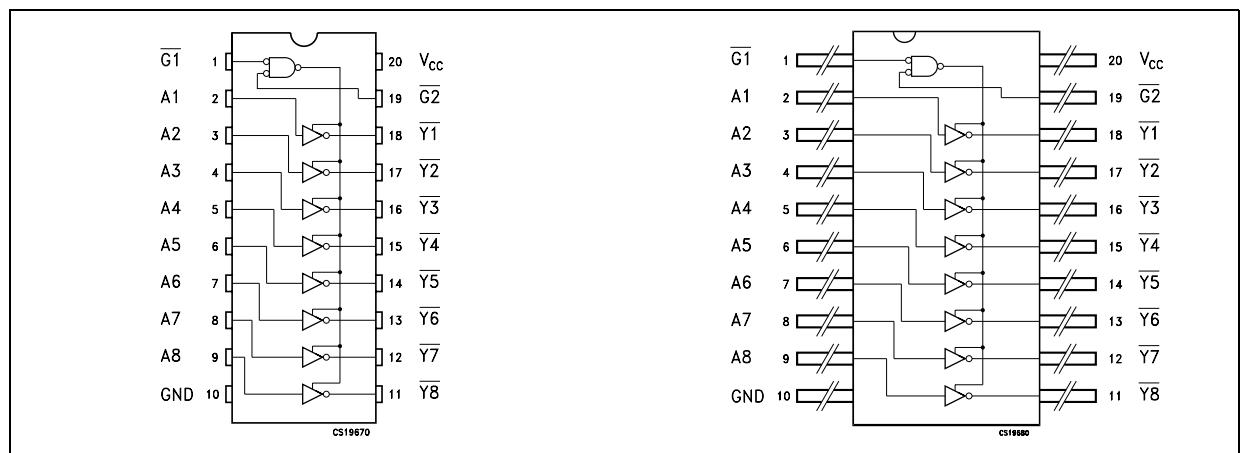
### ORDER CODES

PACKAGE	FM	EM
DILC	M54HC540D	M54HC540D1
FPC	M54HC540K	M54HC540K1

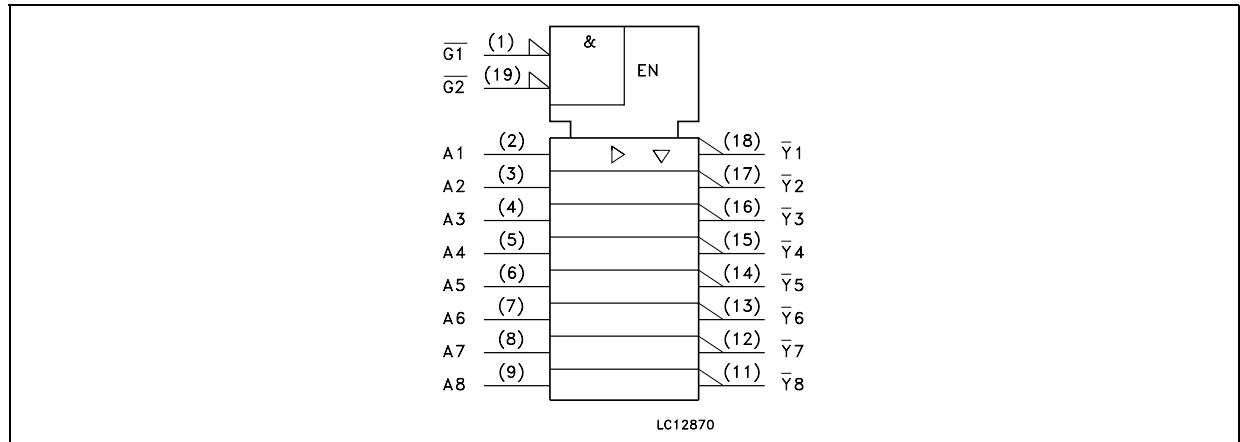
The 3-STATE control gate operates as a two input AND such that if either G1 and G2 are high, all eight output are in the high impedance state. In order to enhance PC board layout the M54HC540 offer a pinout having inputs and outputs on opposite sides of the package.

All inputs are equipped with protection circuits against static discharge and transient excess voltage.

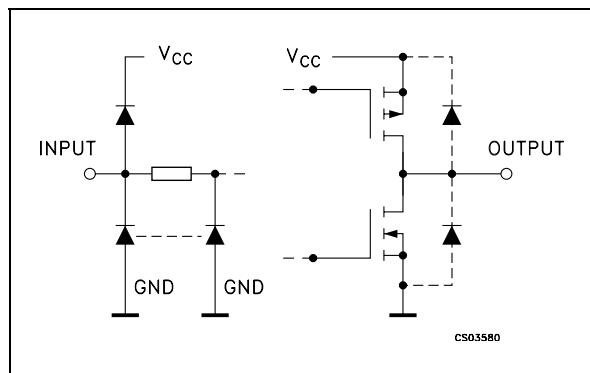
### PIN CONNECTION



**Figure 1: IEC Logic Symbols**



**Figure 2: Input And Output Equivalent Circuit**



**Table 1: Pin Description**

PIN N°	SYMBOL	NAME AND FUNCTION
1, 19	G1, G2	Output Enable Inputs
2, 3, 4, 5, 6, 7, 8, 9	A1 to A8	Data Inputs
18, 17, 16, 15, 14, 13, 12, 11	Y1 to Y8	Bus Outputs
10	GND	Ground (0V)
20	V <sub>CC</sub>	Positive Supply Voltage

**Table 2: Truth Table**

INPUT			OUTPUT
$\overline{G1}$	$\overline{G2}$	$A_n$	$\overline{Y_n}$
H	X	X	Z
X	H	X	Z
L	L	H	L
L	L	L	H

X : Don't Care

Z : High Impedance

**Table 3: Absolute Maximum Ratings**

Symbol	Parameter	Value	Unit
$V_{CC}$	Supply Voltage	-0.5 to +7	V
$V_I$	DC Input Voltage	-0.5 to $V_{CC} + 0.5$	V
$V_O$	DC Output Voltage	-0.5 to $V_{CC} + 0.5$	V
$I_{IK}$	DC Input Diode Current	$\pm 20$	mA
$I_{OK}$	DC Output Diode Current	$\pm 20$	mA
$I_O$	DC Output Current	$\pm 35$	mA
$I_{CC}$ or $I_{GND}$	DC $V_{CC}$ or Ground Current	$\pm 70$	mA
$P_D$	Power Dissipation	420	mW
$T_{stg}$	Storage Temperature	-65 to +150	°C
$T_L$	Lead Temperature (10 sec)	265	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

**Table 4: Recommended Operating Conditions**

Symbol	Parameter	Value	Unit	
$V_{CC}$	Supply Voltage	2 to 6	V	
$V_I$	Input Voltage	0 to $V_{CC}$	V	
$V_O$	Output Voltage	0 to $V_{CC}$	V	
$T_{op}$	Operating Temperature	-55 to 125	°C	
$t_r, t_f$	Input Rise and Fall Time	$V_{CC} = 2.0V$	0 to 1000	ns
		$V_{CC} = 4.5V$	0 to 500	ns
		$V_{CC} = 6.0V$	0 to 400	ns

Table 5: DC Specifications

Symbol	Parameter	Test Condition		Value						Unit	
		$V_{CC}$ (V)		$T_A = 25^\circ C$			$-40 \text{ to } 85^\circ C$		$-55 \text{ to } 125^\circ C$		
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
$V_{IH}$	High Level Input Voltage	2.0		1.5			1.5		1.5		V
		4.5		3.15			3.15		3.15		
		6.0		4.2			4.2		4.2		
$V_{IL}$	Low Level Input Voltage	2.0				0.5		0.5		0.5	V
		4.5				1.35		1.35		1.35	
		6.0				1.8		1.8		1.8	
$V_{OH}$	High Level Output Voltage	2.0	$I_O=-20 \mu A$	1.9	2.0		1.9		1.9		V
		4.5	$I_O=-20 \mu A$	4.4	4.5		4.4		4.4		
		6.0	$I_O=-20 \mu A$	5.9	6.0		5.9		5.9		
		4.5	$I_O=-6.0 mA$	4.18	4.31		4.13		4.10		
		6.0	$I_O=-7.8 mA$	5.68	5.8		5.63		5.60		
$V_{OL}$	Low Level Output Voltage	2.0	$I_O=20 \mu A$		0.0	0.1		0.1		0.1	V
		4.5	$I_O=20 \mu A$		0.0	0.1		0.1		0.1	
		6.0	$I_O=20 \mu A$		0.0	0.1		0.1		0.1	
		4.5	$I_O=6.0 mA$		0.17	0.26		0.33		0.40	
		6.0	$I_O=7.8 mA$		0.18	0.26		0.33		0.40	
$I_I$	Input Leakage Current	6.0	$V_I = V_{CC} \text{ or GND}$			$\pm 0.1$		$\pm 1$		$\pm 1$	$\mu A$
$I_{OZ}$	High Impedance Output Leakage Current	6.0	$V_I = V_{IH} \text{ or } V_{IL}$ $V_O = V_{CC} \text{ or GND}$			$\pm 0.5$		$\pm 5$		$\pm 10$	$\mu A$
$I_{CC}$	Quiescent Supply Current	6.0	$V_I = V_{CC} \text{ or GND}$			4		40		80	$\mu A$

**Table 6: AC Electrical Characteristics ( $C_L = 50 \text{ pF}$ , Input  $t_r = t_f = 6\text{ns}$ )**

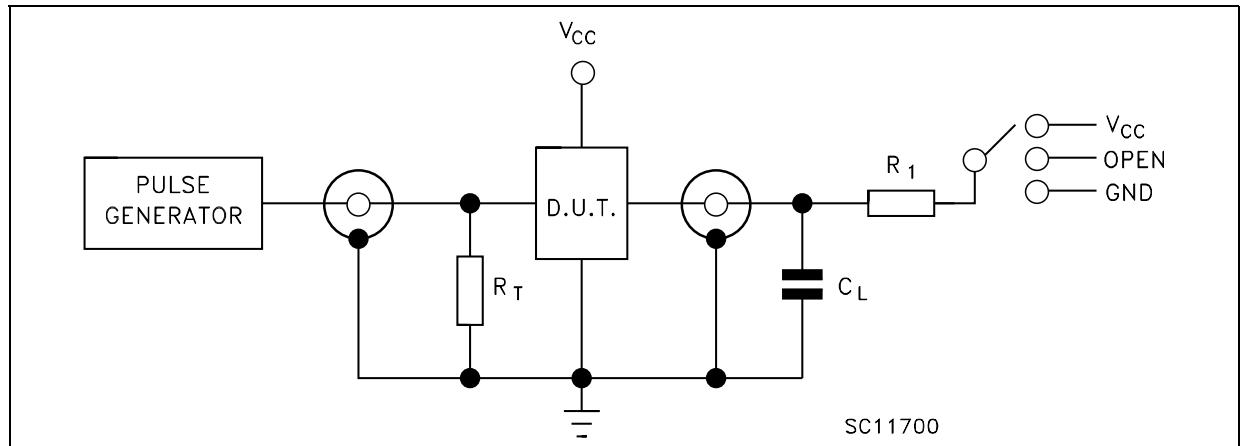
Symbol	Parameter	Test Condition			Value								Unit
		$V_{CC}$ (V)	$C_L$ (pF)		$T_A = 25^\circ\text{C}$			$-40 \text{ to } 85^\circ\text{C}$		$-55 \text{ to } 125^\circ\text{C}$			
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.		
$t_{TLH} t_{THL}$	Output Transition Time	2.0	50			25	60		75		90		ns
		4.5				7	12		19		18		
		6.0				6	10		13		15		
$t_{PLH} t_{PHL}$	Propagation Delay Time	2.0	50			40	85		105		130		ns
		4.5				10	17		21		26		
		6.0				9	14		18		22		
		2.0	150			56	115		145		175		ns
		4.5				14	23		29		35		
		6.0				12	20		25		30		
$t_{PZL} t_{PZH}$	High Impedance Output Enable Time	2.0	50	$R_L = 1 \text{ K}\Omega$		47	110		140		165		ns
		4.5				13	22		28		33		
		6.0				11	19		24		28		
		2.0	150	$R_L = 1 \text{ K}\Omega$		61	135		170		205		ns
		4.5				17	27		34		41		
		6.0				14	23		29		35		
$t_{PLZ} t_{PHZ}$	High Impedance Output Disable Time	2.0	50	$R_L = 1 \text{ K}\Omega$		52	110		140		165		ns
		4.5				15	22		28		33		
		6.0				13	19		24		28		

**Table 7: Capacitive Characteristics**

Symbol	Parameter	Test Condition			Value								Unit
		$V_{CC}$ (V)			$T_A = 25^\circ\text{C}$			$-40 \text{ to } 85^\circ\text{C}$		$-55 \text{ to } 125^\circ\text{C}$			
					Min.	Typ.	Max.	Min.	Max.	Min.	Max.		
$C_{IN}$	Input Capacitance	5.0				5	10		10		10	pF	
$C_{PD}$	Power Dissipation Capacitance (note 1)	5.0				31						pF	

1)  $C_{PD}$  is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation.  $I_{CC(\text{opr})} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/8$  (per gate)

Figure 3: Test Circuit



TEST	SWITCH
$t_{PLH}, t_{PHL}$	Open
$t_{PZL}, t_{PLZ}$	$V_{CC}$
$t_{PZH}, t_{PHZ}$	GND

$C_L = 50\text{pF}/150\text{pF}$  or equivalent (includes jig and probe capacitance)

$R_1 = 1\text{K}\Omega$  or equivalent

$R_T = Z_{\text{OUT}}$  of pulse generator (typically  $50\Omega$ )

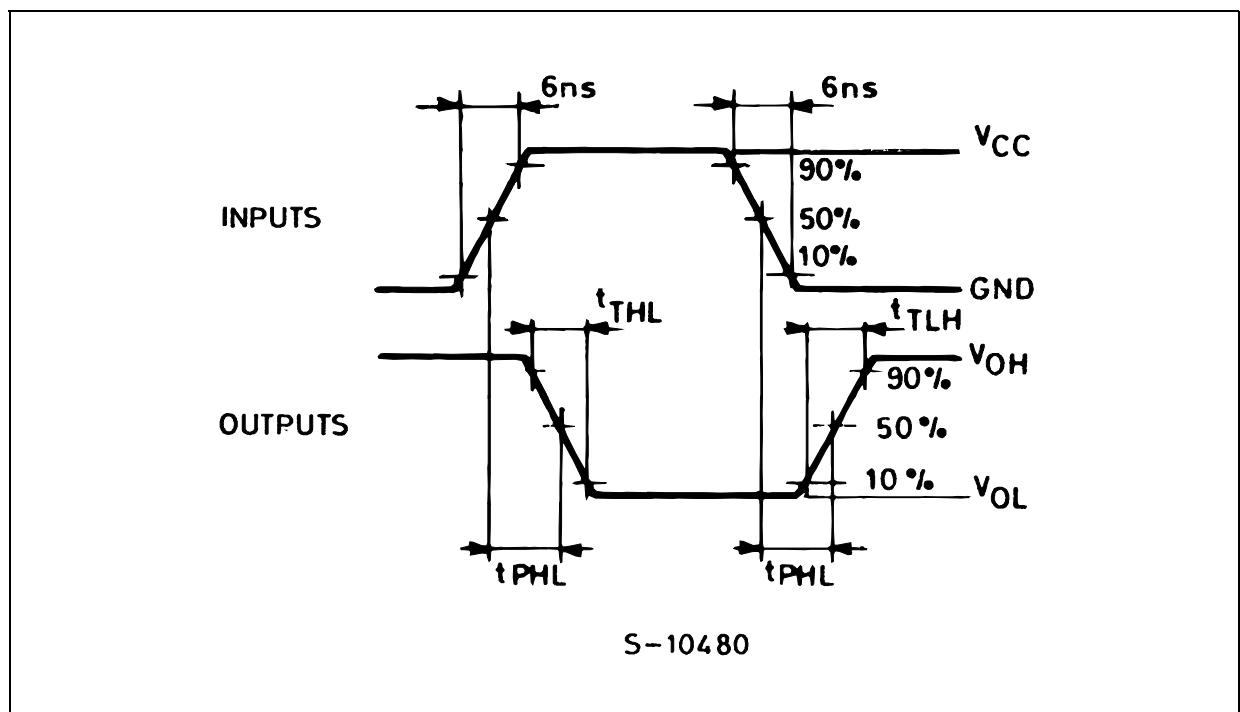
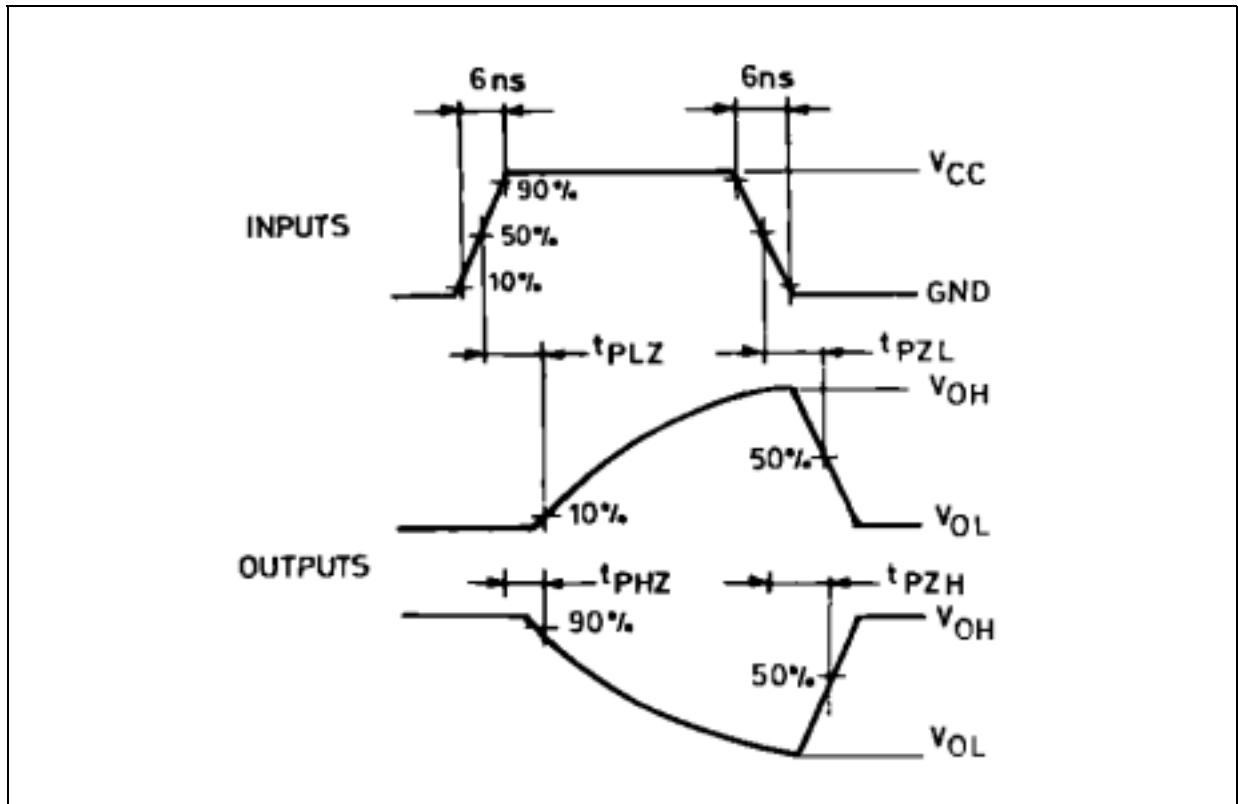
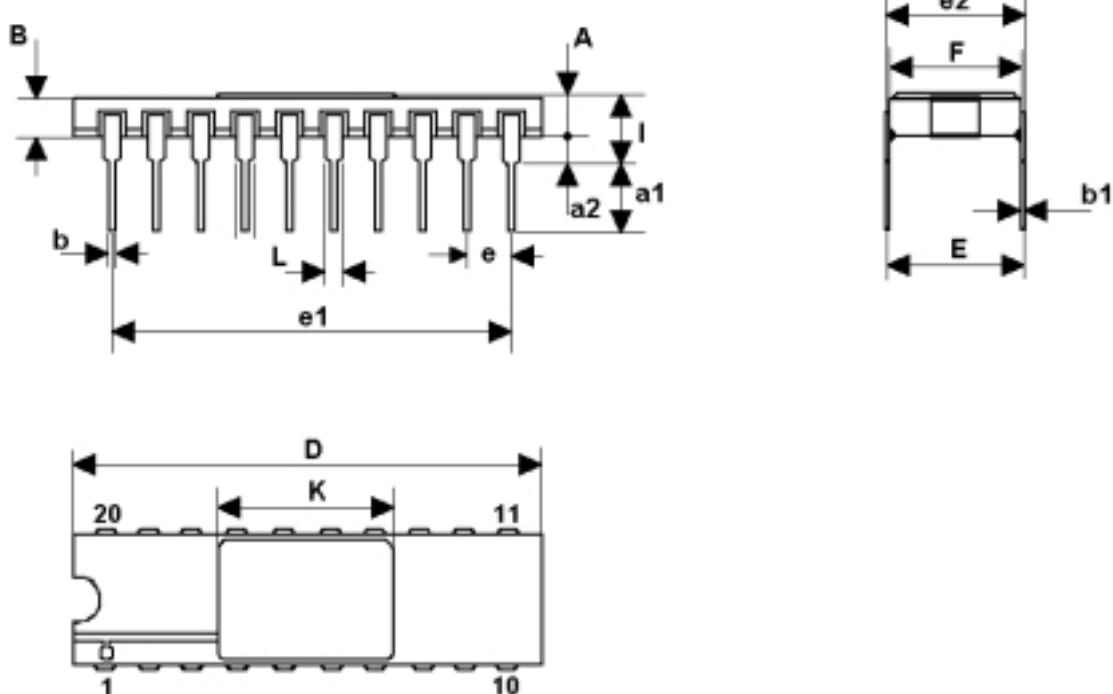
Figure 4: Waveform - Propagation Delay Times ( $f=1\text{MHz}$ ; 50% duty cycle)

Figure 5: Waveform - Output Enable And Disable Time (f=1MHz; 50% duty cycle)



## DILC-20 MECHANICAL DATA

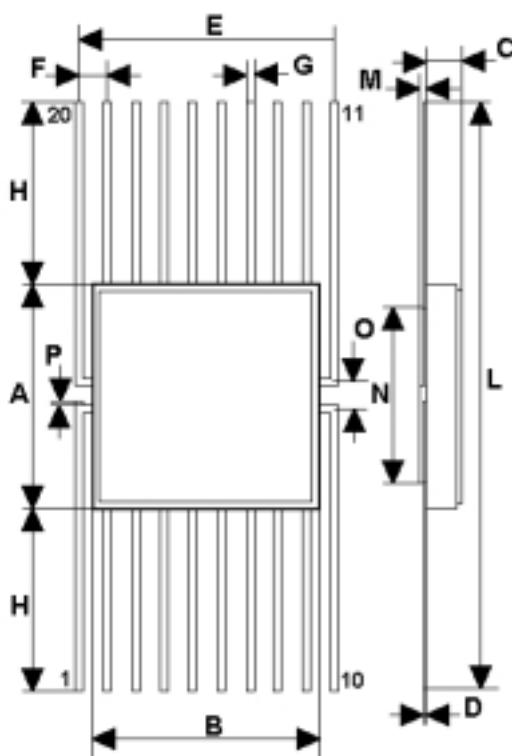
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	2.1		2.71	0.083		0.107
a1	3.00		3.70	0.118		0.146
a2	0.63	0.88	1.14	0.025	0.035	0.045
B	1.93	2.03	2.23	0.076	0.080	0.088
b	0.40	0.45	0.50	0.016	0.018	0.020
b1	0.20	0.254	0.30	0.008	0.010	0.012
D	25.14	25.40	25.65	0.990	1.000	1.010
E	7.36	7.62	7.87	0.290	0.300	0.310
e		2.54			0.100	
e1	22.73	22.86	22.99	0.895	0.900	0.905
e2	7.62	7.87	8.12	0.300	0.310	0.320
F	7.29	7.49	7.70	0.287	0.295	0.303
I			3.86			0.152
K	11.30		11.56	0.445		0.455
L	1.14	1.27	1.40	0.045	0.050	0.055



0016178J

## FPC-20 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	9.98	10.16	10.34	0.393	0.400	0.407
B	9.98	10.16	10.34	0.393	0.400	0.407
C	1.45	1.61	1.78	0.57	0.63	0.070
D	0.10	0.127	0.18	0.004	0.005	0.007
E	11.30	11.43	11.56	0.445	0.450	0.455
F		1.27			0.050	
G	0.38	0.43	0.48	0.015	0.017	0.019
H	7.24		8.16	0.285		0.320
L	24.46		26.67	0.960		1.050
M	0.45	0.50	0.55	0.018	0.020	0.022
N		7.87			0.310	
O	1.14	1.27	1.40	0.045	0.050	0.055
P	0.10	0.18	0.25	0.004	0.007	0.010



**Table 8: Revision History**

Date	Revision	Description of Changes
14-May-2004	1	First Release

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